

## RLS-73

### FEATURES :

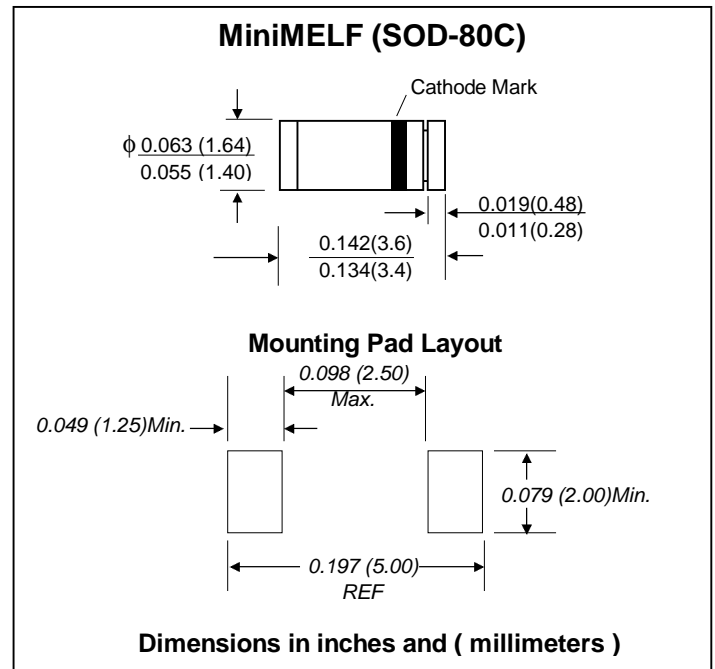
- \* Silicon Epitaxial Planar Diode
- \* High reliability
- \* Low reverse current
- \* Low forward voltage drop
- \* High speed ( $T_{rr} = 1.2 \text{ ns Typ.}$ )
- \* Pb / RoHS Free

### MECHANICAL DATA :

Case: MiniMELF Glass Case (SOD-80)

Weight: approx. 0.05g

## HIGH SPEED SWITCHING DIODE



### Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	$V_{RM}$	90	V
Maximum Reverse Voltage	$V_R$	80	V
Peak Forward Current	$I_{FM}$	400	mA
Average Forward Current	$I_{F(AV)}$	130	mA
Surge Forward Current (1s)	$I_{SURGE}$	600	mA
Power Dissipation	$P_D$	300	mW
Junction Temperature	$T_J$	175	°C
Storage Temperature Range	$T_{STG}$	-65 to + 175	°C

### Electrical Characteristics ( $T_a = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Reverse Current	$I_R$	$V_R = 80 \text{ V}$	-	-	0.5	$\mu\text{A}$
Forward Voltage	$V_F$	$I_F = 100 \text{ mA}$	-	-	1.2	V
Capacitance between terminals	$C_T$	$f = 1\text{MHz} ; V_R = 0.5 \text{ V}$	-	-	2	pF
Reverse Recovery Time	$T_{rr}$	$I_F = 10 \text{ mA} , V_R = 6 \text{ V} , R_L = 50\Omega$	-	-	4	ns

## RATING AND CHARACTERISTIC CURVES ( RLS-73 )

FIG.1 - REVERSE RECOVERY TIME ( $T_{rr}$ ) MEASUREMENT CIRCUIT

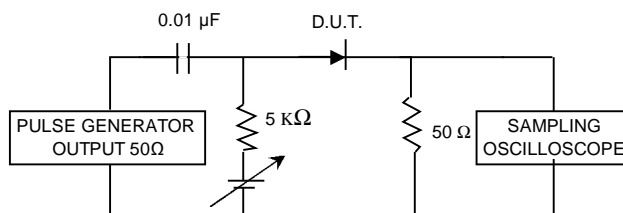


FIG.2 - REVERSE CHARACTERISTICS

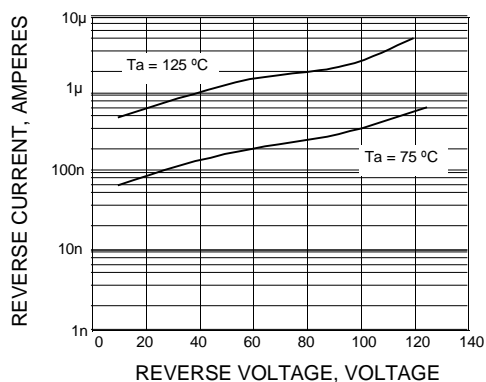


FIG.3 - SURGE CURRENT CHARACTERISTICS

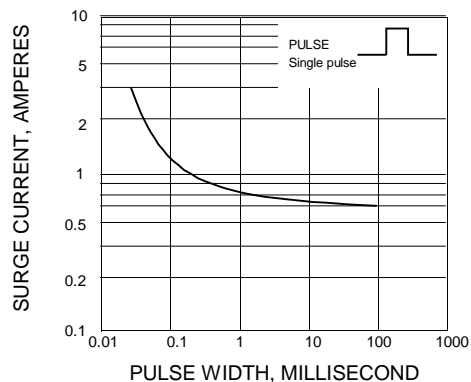


FIG.4 - FORWARD CHARACTERISTICS

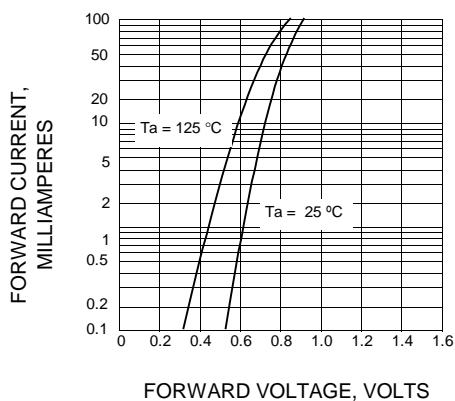


FIG.5 - CAPACITANCE BETWEEN TERMINALS CHARACTERISTICS

